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	APPLICANT TSUCHIYA et al.	
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U.S. Patent Documents

Examiner Initial		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

Foreign Patent Documents

Examiner Initial		DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
MS		10-84170	8/11/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

MS		R. Bhat et al, "High-Performance 1.3 μm AlGaInAs/InP Strained Quantum Well Lasers Grown by Organometallic Chemical Vapor Deposition", Journal of Crystal Growth (1004), pp. 858-865
		P.J.A. Thijs et al., "High Performance Buried Heterostructure λ=1.5 μm InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", 10th International Conference on Indium Phosphide and Related Materials (1996) ThA2-2, pp. 765-768
		Tawee Tanbun-Ek et al., "High Performance Buried Heterostructure 1.55 μm Wavelength AlGaInAs/InP Multiple Quantum Well Lasers Grown Entirely by NOVPE Technique", 10th International Conference on Indium Phosphide and Related Materials (May 1998) ThP-48, pp. 702-705
MS		C. E. Zah et al., "High-Temperature Modulation Dynamics of 1.3 μm $Al_xGa_yIn_{1-x-y}As$/InP Compressive-Strained Multiple-Quantum-Well Lasers", 14th International Semiconductor Laser Conference (1994), TH 1.3, pp. 215-216

EXAMINER	DATE CONSIDERED
[signature]	7/26/05

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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